

Amendments to the Claims

1. (Original): A substrate susceptor for receiving a semiconductor substrate for selective epitaxial silicon-comprising depositing thereon, the depositing comprising measuring emissivity of the susceptor from at least one susceptor location in a non-contacting manner the susceptor comprising:

a body having a front substrate receiving side, a back side, and a peripheral edge; and

at least one susceptor location from which emissivity is to be measured being received on at least one of the front substrate receiving side, the back side, and the edge; said at least one susceptor location comprising an outermost surface comprising a material upon which selective epitaxial silicon will not deposit upon during selective epitaxial silicon depositing on a semiconductor substrate received by the susceptor for at least an initial thickness of epitaxial silicon depositing on said substrate.

2. (Original): A substrate susceptor for receiving a semiconductor substrate for selective epitaxial silicon-comprising depositing thereon, the depositing comprising measuring emissivity of the susceptor from at least one susceptor location in a non-contacting manner, the susceptor comprising:

a body having a front substrate receiving side, a back side, and a peripheral edge, the body comprising SiC coated graphite; and

at least one susceptor location from which emissivity is to be measured being received on at least the back side, said at least one susceptor location comprising an outermost surface layer received over the SiC and comprising a material upon which selective epitaxial silicon will not deposit upon during selective epitaxial silicon depositing or a semiconductor substrate received by the susceptor for at least an initial thickness of epitaxial silicon depositing on said substrate.

3. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon by thermal deposition comprising susceptor back side radiant heating, the susceptor comprising a body having a front substrate receiving side, a back side, and a peripheral edge; the body comprising multiple materials having at least two different thermal conductivities; an outer material received across the back side having a higher thermal conductivity than an immediately adjacent material of the body, the outer material comprising at least one of polycrystalline diamond and copper.

4. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon by thermal deposition comprising susceptor back side radiant heating, the susceptor comprising a body having a front substrate receiving side, a back side, and a peripheral edge; the body comprising multiple materials having at least two different thermal conductivities; an outer material received across the back side having a higher thermal conductivity than an immediately adjacent material of the body, the outer material not being received over an outer portion of any of the front substrate receiving side.

5. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon by thermal deposition comprising susceptor back side radiant heating, the susceptor comprising a body having a front substrate receiving side, a back side, and a peripheral edge; the body comprising multiple materials having at least two different thermal conductivities; an outer material received across the back side having a thermal conductivity which is at least three times higher than that of an immediately adjacent material of the body.

6. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon by thermal deposition comprising susceptor back side radiant heating, the susceptor comprising a body having a front substrate receiving side, a back side, and a peripheral edge; the body comprising SiC coated graphite, an outer material received across the back side over the SiC, the outer material having a higher thermal conductivity than that of the SiC and the graphite.

7. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon by thermal deposition comprising heating of the susceptor, the susceptor comprising a body having a front substrate receiving side, a back side, and a peripheral edge; the body comprising multiple materials which have at least two different thermal conductivities and are received at different radial locations and not across an entirety of either the body front side or body back side.

Claims 8 and 9 (Canceled).

10. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon, the susceptor comprising a body having a front substrate receiving side, a back side, and a peripheral edge; the body comprising at least one solid portion therethrough that is transparent to infrared radiation.

Claims 11 and 12 (Canceled).

13. (Original): A substrate susceptor for receiving a semiconductor substrate to be deposited upon, the susceptor comprising a body having a front substrate receiving side face, a back side face, and a peripheral edge; the body comprising a ring having a radial inner portion at least a radial majority of which is non-solid space extending from the front side face to the back side face.

Claims 14-22 (Canceled).